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BT138S-XXXE(MS)

Product specification





DESCRIPTION

The BT138S-XXXE(MS) SCR series with the parallel resistor between Gate and Cathode are espe -cially recommended for use on straight hair, igniter, anion generator, etc.

MAIN FEATURES

Symbol	Value	Unit
It(RMS)	12	А
Vdrm /Vrrm	600/800	V

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking	
1 3 3 3 3 3 3 3 3 3 3 3 3 3	O T2(2) G(3) O T1(1)	MSKSEMI BT138S-600E MS XXX	MSKSEMI BT138S-800E MS XXX
5		BT138S-600E(MS)	BT138S-800E(MS)
Notes :XXX represents the order code.			

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Storage junction temperature range	Tstg	-40-150	°C	
Operating junction temperature rang	je	Tj	-40-125	°C
Repetitive peak off-state voltage(Tj=	25℃)	Vdrm	600/800	V
Repetitive peak reverse voltage(Tj=2	25℃)	Vrrm	600/800	V
RMS on-state current(TC=95℃)	IT(RMS)	12	A	
Non repetitive surge peak on-state current (full cycle, F=50Hz)		Ітѕм	95	А
Pt value for fusing (tp=10ms)		l²t	45	A ² s
Critical rate of rise of on-state	I - II -III		50	A/up
current(Ig=2×Igт)	IV	dl/dt	10	— A∕µs
Peak gate current	Ідм	2	А	
Average gate power dissipation		P _{G(AV)}	0.5	W
Peak gate power		Рсм	5	W



ELECTRICAL CHARACTERISTICS (T_j=25 $^{\circ}$ C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
1		I - II -III	MAX	10	mA
lgт	V₀=12V R∟=33Ω	IV		25	
Vgt		ALL	MAX	1.5	V
Vgd	VD=VDRM Tj=125 ℃ RL=3.3KΩ	ALL	MIN	0.2	V
l∟ lg=1.2Igт	I - III		30	m۸	
	IG=1.2IGT	II- IV	MAX	40	mA
Ін	h=100mA		MAX	25	mA
dV/dt	V _D =2/3V _{DRM} Gate Open Tj=125℃		MIN	50	V/µs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
Vтм	Iтм=15Atp=380µs	T j =25 ℃	1.6	V
Idrm		T j =25 ℃	5	μA
IRRM		Tj=125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-c)	junction to case(AC)	1.7	°C/W
Rth(j-a)	junction to ambient	70	°C/W



FIG.1: Maximum power dissipation versus RMS on-state current

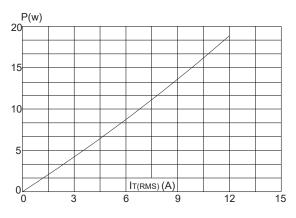


FIG.3: Surge peak on-state current versus number of cycles

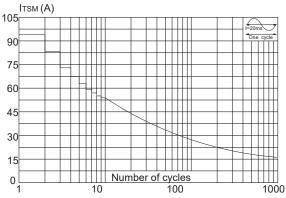
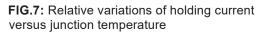
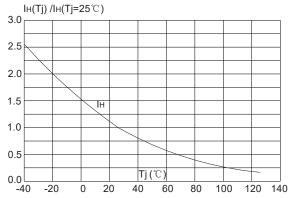
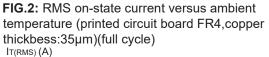


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I²t(I - II - III:dI/dt < 50A/µs; IV:dI/dt < 10A/µs)







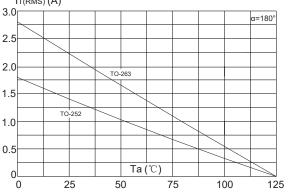


FIG.4: On-state characteristics (maximum values)

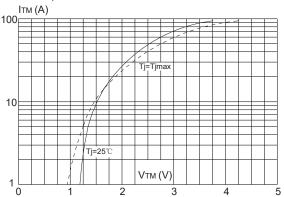
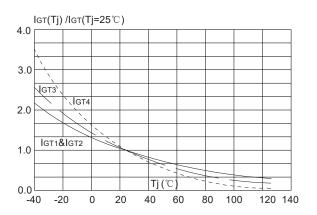
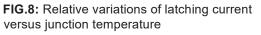
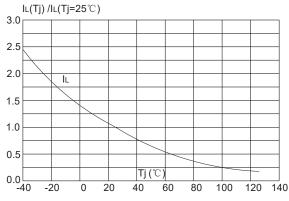


FIG.6: Relative variations of gate trigger current versus junction temperature

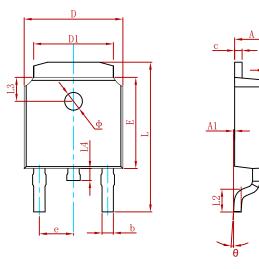


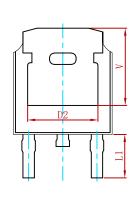






PACKAGE MECHANICAL DATA

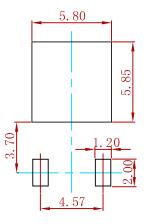




Cumhal	Dimensions	In Millimeters	Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
С	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830	REF.	0.190 REF.	
E	6.000	6.200	0.236	0.244
е	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900	REF.	0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063	REF.
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207	REF.

h

Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BT138S-XXXE(MS)	TO-252	2500



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